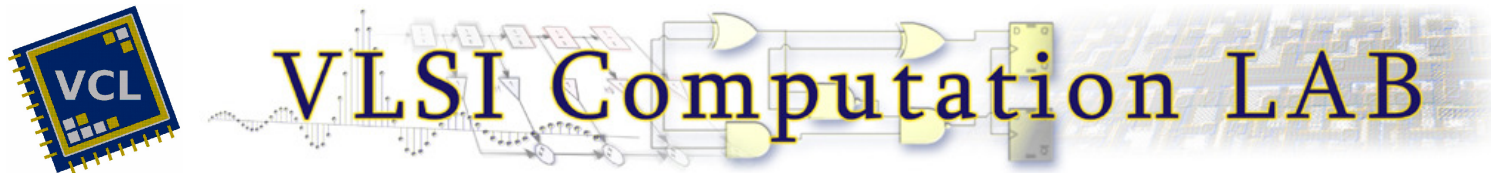


# Dynamic Voltage and Frequency Scaling Circuits with Two Supply Voltages

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# Outline

- **Background and Motivation**
- Implementation
- Results



# DVFS Background

$$P_{dyn} = \alpha C V_{dd}^2 f$$

$$E = C V_{dd}^2$$

$$t_d \approx C V_{dd} / (V_{dd} - V_t)^\alpha$$

$$V_{dd} \downarrow f \downarrow \Rightarrow P_{dyn,leak} \downarrow$$

$$V_{dd} \downarrow \Rightarrow E \downarrow$$

$$V_{dd} \downarrow \Rightarrow t_d \uparrow f_{max} \downarrow$$

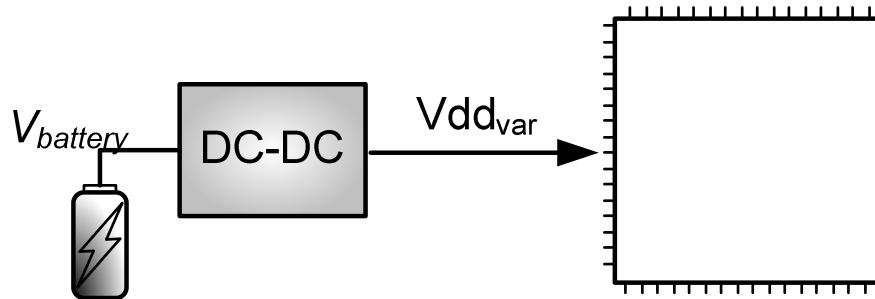
Reducing supply voltage:

- Reduces power and energy dissipation
- Reduces maximum clock frequency due to increased gate delay

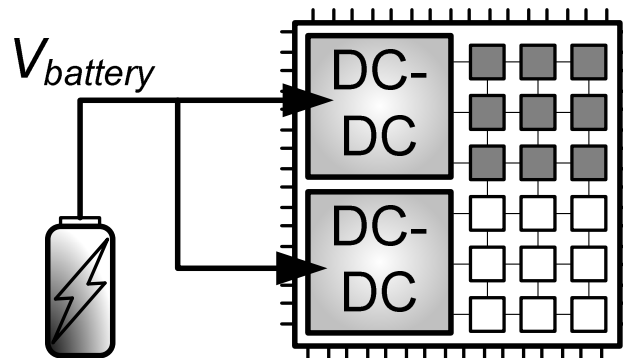


# Other DVFS Schemes

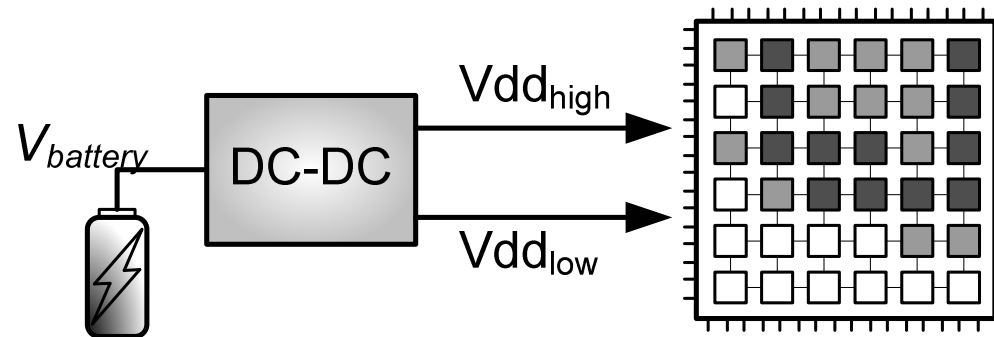
## Scheme 1: Off-chip DC-DC Converter



## Scheme 2: On-chip DC-DC Converter



# Presented DVFS Scheme



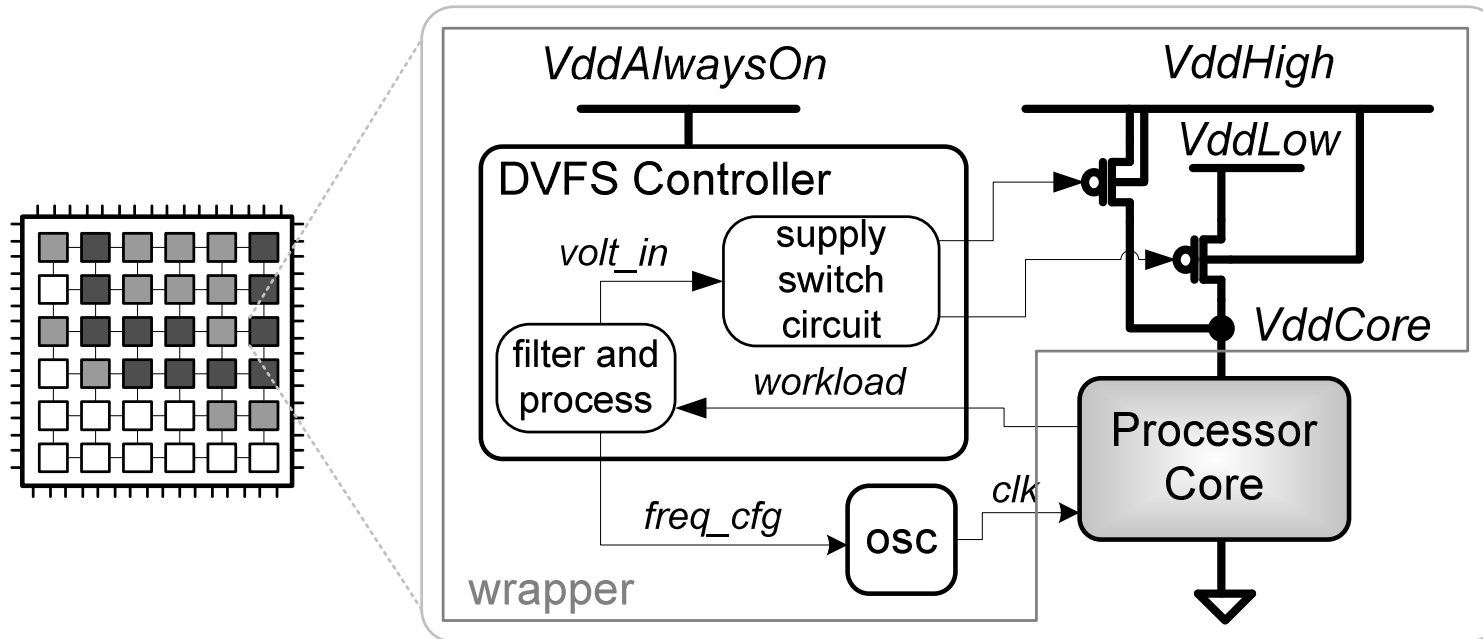
- Fine grain voltage scaling
  - Maximum power/energy reduction with minimum performance overhead
- Small area overhead by using an off-chip DC-DC converter, and switching between voltages on-chip

# Outline

- Background and Motivation
- **Implementation**
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# Implementation Schematic



- Voltage scaling with 2 discrete voltage levels
- Supply switching with PMOS power gates
- Automated DVFS based on workload
- Wrapper powered by always on power supply

# Power Gate Sizing

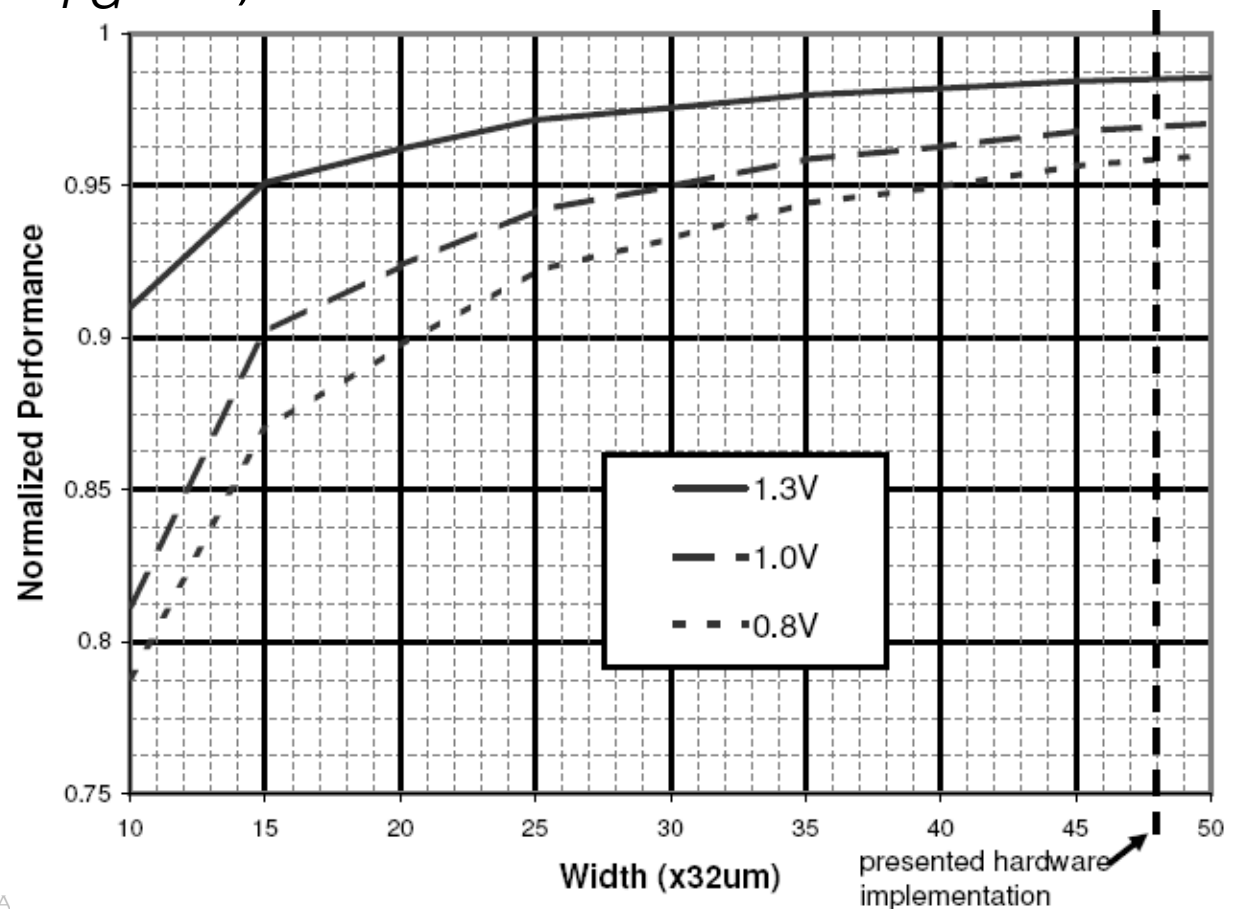
$$V_{PG} = I_{PG} R_{PG}$$

$$R_{PG} \sim L/W$$

$$t_d \approx CV_{dd}/(V_{dd} - V_{PG} - V_t)^\alpha$$

$$W/L \uparrow \quad V_{PG} \downarrow \quad t_d \downarrow \quad f_{max} \uparrow$$

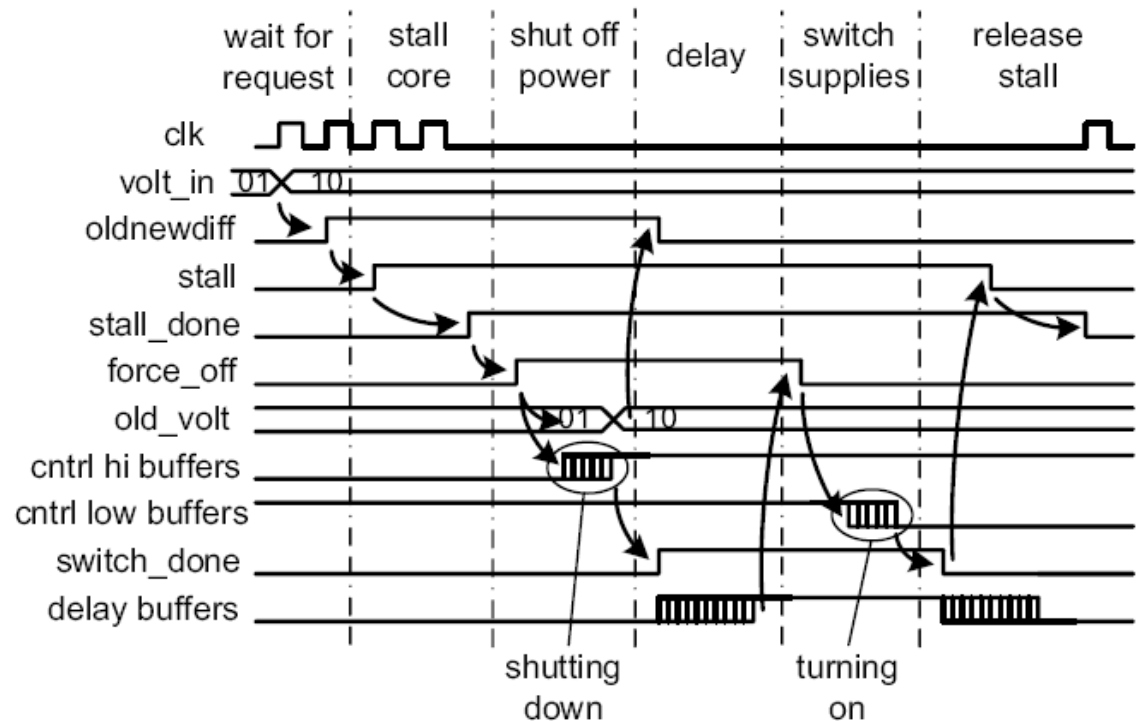
Voltage drop can be reduced by making  $W/L$  as large as possible  
 → done by adding parallel power gates





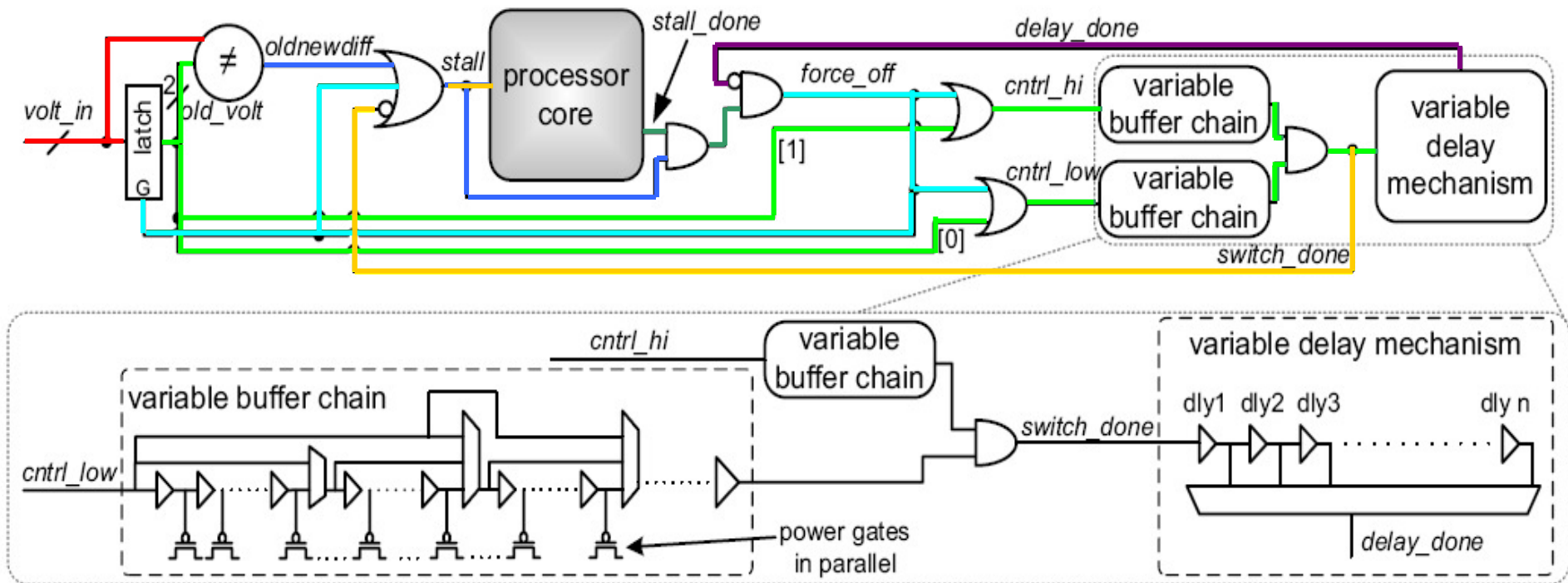
# Supply Switching Scheme

- Supply grid noise:
  - Gradually switch between power supplies
- Shorting between power supplies:
  - Shut both power supplies off and wait for some time before switching
- Data corruption:
  - Stall the processor core before switching between power supplies

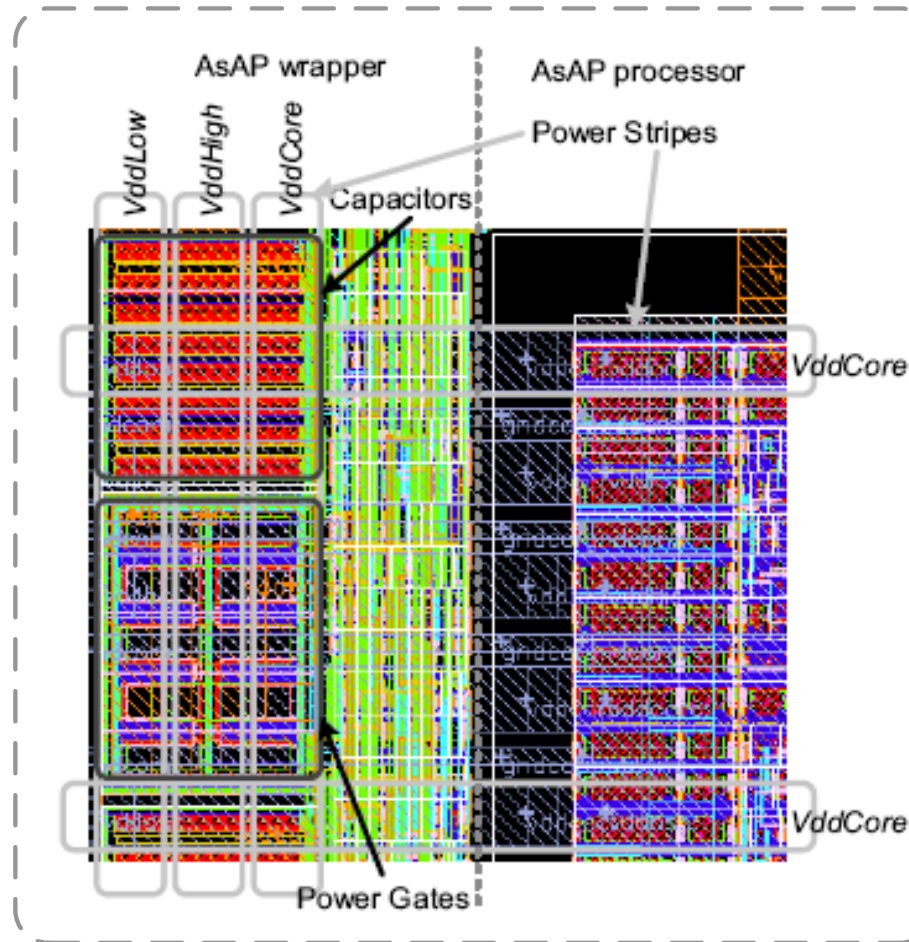


# Dynamic Run-time Supply Switching Circuit

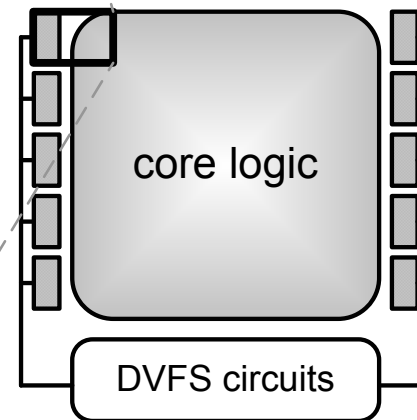
- Wait for request
- Delay
- Stall core
- Supply switch
- Shut off power
- Release stall



# Physical Implementation



- Power gates are positioned along vertical power stripes
- Core power is supplied with horizontal power stripes



# Outline

- Background and Motivation
- Implementation
- **Results**



# Implementation Results

- Implemented in 65nm CMOS technology
- DVFS circuit area is 12% of AsAP processor's core area
- 66% of the DVFS circuit area is power gates and decoupling capacitors
- Maximum power consumption of DVFS logic is 4% of AsAP processor core's power



# Energy Consumption Metric

- $P_{dyn} = \alpha CVdd^2 f$
- $E = CVdd^2$
- **Energy reduction is possible only with voltage scaling**
  
- $EDP = E * t_d$
- **Energy delay product measures the effect of increased delay with DVFS**



# Measurement of Relative Energy Delay Product

$$EDP_{rel} = \left( \frac{\beta Vdd_{Low}^2 + (1 - \beta) Vdd_{High}^2}{Vdd_{High}^2} \right) \left( \frac{t_{dvfs}}{t_{orig}} \right)$$

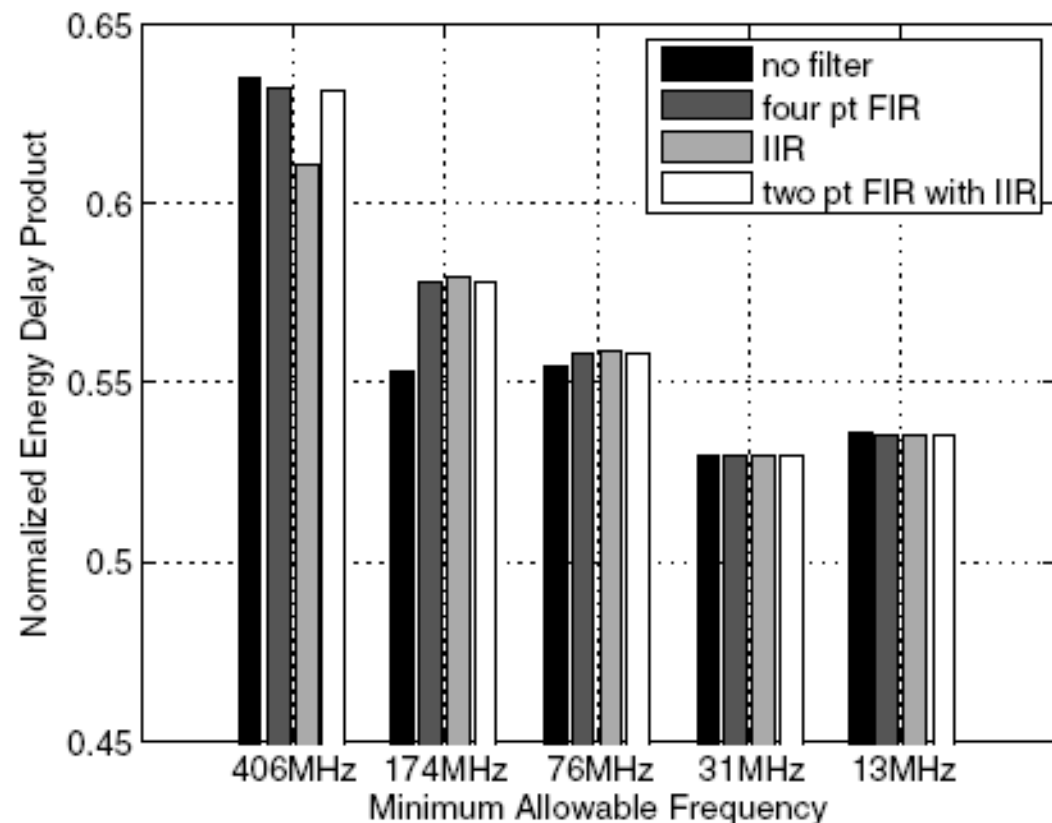
- $\beta$  is the fraction of time operating on the lower voltage
- $t_{dvfs}$  is the total run time with DVFS
- $t_{orig}$  is the total run time without DVFS.



# 9 Processor JPEG Application

$V_{ddhigh} = 1.3V$ ,  $V_{ddlow} = 0.8V$   
Maximum Frequency = 1.05 GHz

- Lower minimum frequency  $\rightarrow$  Increase in time on lower supply
- *EDP* decreases as the minimum frequency decreases up until 13 MHz
- *EDP* increases as the performance overhead outweighs the energy savings

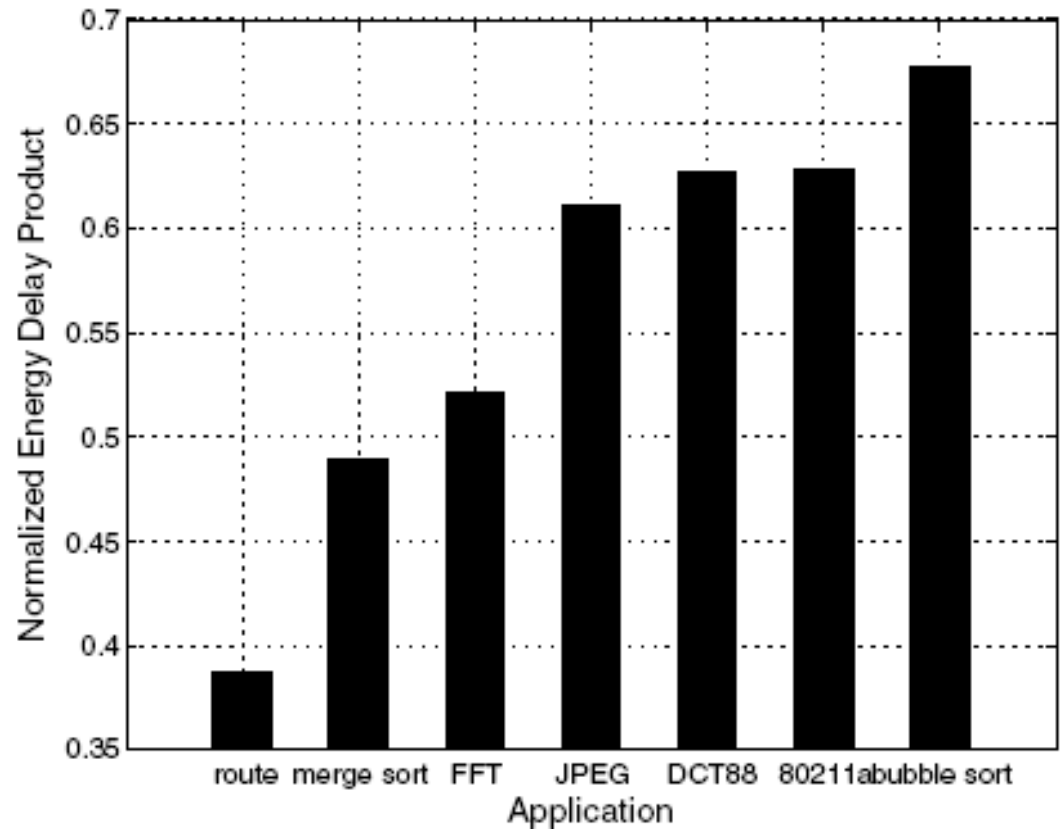




# Various Applications

- *EDP* dependent on workload variations
- Increase in workload variation → Increase in switching between supplies → Increase in performance overhead → Increase in *EDP*

$V_{ddhigh} = 1.3V$ ,  $V_{ddlow} = 0.8V$   
Maximum Frequency = 1.05 GHz



# Summary

- DVFS with 2 supply voltages
- Power gates sized to reduce perf. loss
- Robust supply switching circuit
- EDP is reduced by 48% on a 9 processor JPEG application
- Functional in silicon at 65nm node



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